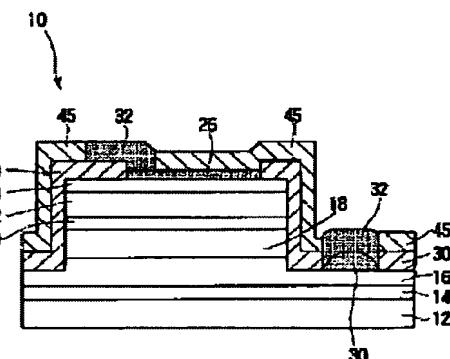


SEMICONDUCTOR LIGHT EMITTING ELEMENT, SEMICONDUCTOR LIGHT EMITTING DEVICE AND MANUFACTURE THEREOF**Publication number:** JP11087778**Publication date:** 1999-03-30**Inventor:** KAWAMOTO SATOSHI; NITTA KOICHI; KONNO KUNIYAKI; SUZUKI NOBUHIRO**Applicant:** TOKYO SHIBAURA ELECTRIC CO**Classification:**- **international:** H01L33/00; H01L33/00; (IPC1-7): H01L33/00; H01S3/18- **european:****Application number:** JP19970237492 19970902**Priority number(s):** JP19970237492 19970902**Report a data error here****Abstract of JP11087778**

PROBLEM TO BE SOLVED: To make a light emission wavelength stable and allow light emission with high brightness in a wavelength in a region from visible light to infrared rays. **SOLUTION:** A fluorescent substance is included or deposited in any part of the semiconductor light emitting element 10. The fluorescent substance has an absorption peak in a wavelength band of 340 to 380 nm. Therefore, in order to effectively convert wavelength by the fluorescent substance, a light emitting layer 20 desirably emits ultraviolet rays of a wavelength band of 308 nm or less. A site to include the fluorescent substance in the semiconductor element 10 may be a p-side electrode layer 26, first. Then, a silicon oxide layer 45 or a current preventing layer 30 may follow. Alternatively any of respective semiconductor layers 14 to 24 may follow. A substrate 12 may follow further.



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